

5. (Amended) The color cathode-ray tube as claimed in claim 1 [or 3], wherein the half etching line is formed on each of both surfaces at the non-effective area of the shadow mask.

9. (Amended) The color cathode-ray tube as claimed in claim 1 [or 3], wherein the distance between the effective area and the half etching lines corresponds to 100-200 μ m.

10. (Amended) The color cathode-ray tube as claimed in claim 1 [or 3], wherein the width of the half etching line is 50-100 μ m.

11. (Amended) The color cathode-ray tube as claimed in claim 1 [or 3], wherein there are at least two half etch lines, the distance between the two half etching lines corresponding from the thickness of the shadow mask to twice the thickness thereof.

13. (Amended) The color cathode-ray tube as claimed in claim 1 [or 3], wherein the etched depth of the half etching line corresponds to 10-35% of the thickness of the shadow mask.

15. (Amended) The color cathode-ray tube as claimed in claim 3 [or 7], wherein the radius of curvature of the corner of the half etching line is 0.8-3mm.

096944-02004
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Clean Set of Amended Claims

4. (Amended) The color cathode-ray tube as claimed in claim 1, wherein the non-effective area is bent to have the a skirt attached to a frame, and the half etching line is placed between the bent portion and the portion attached to the frame at the skirt.

5. (Amended) The color cathode-ray tube as claimed in claim 1, wherein the half etching line is formed on each of both surfaces at the non-effective area of the shadow mask.

9. (Amended) The color cathode-ray tube as claimed in claim 1, wherein the distance between the effective area and the half etching lines corresponds to 100-200 μ m.

10. (Amended) The color cathode-ray tube as claimed in claim 1, wherein the width of the half etching line is 50-100 μ m.

11. (Amended) The color cathode-ray tube as claimed in claim 1, wherein there are at least two half etch lines, the distance between the two half etching lines corresponding from the thickness of the shadow mask to twice the thickness thereof.

$$R_e^3$$

etched depth of the half etching line corresponds to 10-35% of the thickness of the shadow mask.

at

radius of curvature of the corner of the half etching line is 0.8-3mm.

DECLASSIFICATION AUTHORITY